Application Note No. 001

SIEGET25 Low Noise Amplifier with BFP420 Transistor at 2.4 GHz

Small Signal Discretes



Edition 2007-01-08

Published by Infineon Technologies AG 81726 München, Germany © Infineon Technologies AG 2007. All Rights Reserved.

LEGAL DISCLAIMER

THE INFORMATION GIVEN IN THIS APPLICATION NOTE IS GIVEN AS A HINT FOR THE IMPLEMENTATION OF THE INFINEON TECHNOLOGIES COMPONENT ONLY AND SHALL NOT BE REGARDED AS ANY DESCRIPTION OR WARRANTY OF A CERTAIN FUNCTIONALITY, CONDITION OR QUALITY OF THE INFINEON TECHNOLOGIES COMPONENT. THE RECIPIENT OF THIS APPLICATION NOTE MUST VERIFY ANY FUNCTION DESCRIBED HEREIN IN THE REAL APPLICATION. INFINEON TECHNOLOGIES HEREBY DISCLAIMS ANY AND ALL WARRANTIES AND LIABILITIES OF ANY KIND (INCLUDING WITHOUT LIMITATION WARRANTIES OF NON-INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHTS OF ANY THIRD PARTY) WITH RESPECT TO ANY AND ALL INFORMATION GIVEN IN THIS APPLICATION NOTE.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



SIEGET25 Low Noise Amplifier with BFP420 Transistor at 2.4 GHz													
Revisio	n History: 2007-01-08, Rev. 2.0												
Previou	Previous Version: 2000-07-27												
Page	Subjects (major changes since last revision)												
All	Document layout change												

Trademarks

SIEGET® is a registered trademark of Infineon Technologies AG.

Application Note 3 Rev. 2.0, 2007-01-08



1 Low Noise Amplifier with BFP420 Transistor at 2.4 GHz

The SIEMENS Grounded Emitter Transistor Line is a completely new generation of silicon bipolar junction RF-transistors. This application note describes a low-noise amplifier with the following characteristics¹⁾:

Gain: 13.6 dBNoise Figure: 1.4 dB

· unconditionally stable at all frequencies

In order to match the input and output ports, a well defined emitter inductance is used as negative feedback. This acts to stabilise the transistor, decreasing the usable gain. Without feedback the gain of the amplifier would be 17.5 dB but matching and stability would be degraded. As the feedback is lossless, the amplifier noise figure would remain 1.4 dB

A double-transistor active stabilisation is used for DC biasing, whose provides a temperature stable current source.

Figure 1 shows the circuit diagram. **Figure 2** shows the circuit layout whose substrate material is PTFE ε_r = 2.45, H = 0.38 mm, e.g. Di-CLAD 527, 15 mil; Scale: 2:1 (40 mm x 40 mm real size). **Figure 3** shows the part mounting plan.

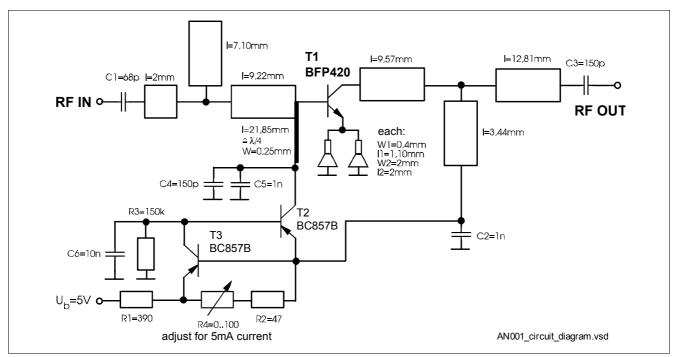


Figure 1 Circuit diagram

Application Note 4 Rev. 2.0, 2007-01-08

^{1) @} f = 2.4 GHz, Vce = 2.5 V, IC = 5 mA



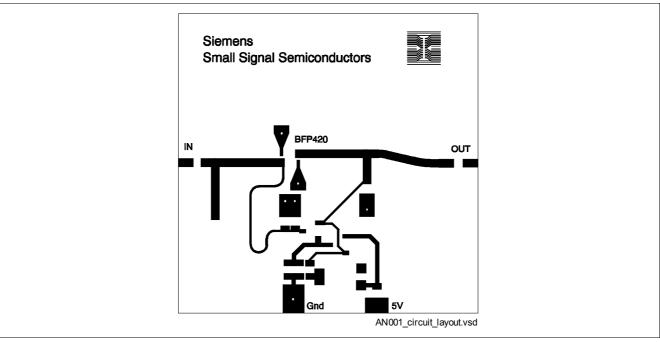


Figure 2 Circuit layout

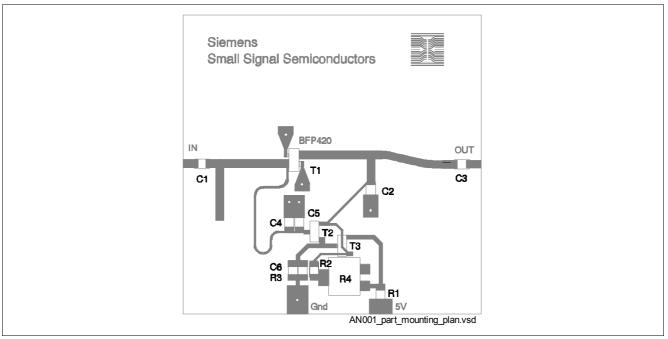


Figure 3 Part mounting plan

Application Note 5 Rev. 2.0, 2007-01-08



Table 1 List of all used SMD components

Name	Type, Package (Supplier)									
C1	68 pF 0805 (Epcos)									
C2	1 nF 0805 (Epcos)									
C3	150 pF 0805 (Epcos)									
C4	150 pF 0805 (Epcos)									
C5	1 nF 0805 (Epcos)									
C6	10 nF 0805 (Epcos)									
R1	390 Ω 0805 (Epcos)									
R2	47 Ω 0805 (Epcos)									
R3	150 kΩ 0805 (Epcos)									
R4	0100 Ω Trimmer (Beckmann)									
T1	BFP420 SOT343 (Infineon)									
T2	BC857B SOT23 (Infineon)									
T3	BC857B SOT23 (Infineon)									

The following diagrams show power-gain, input- and output matching

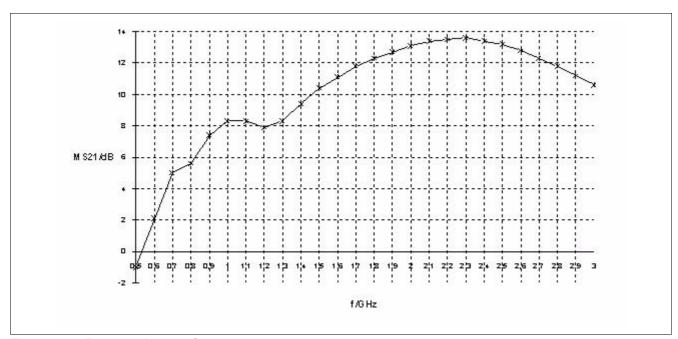


Figure 4 Power gain over frequency



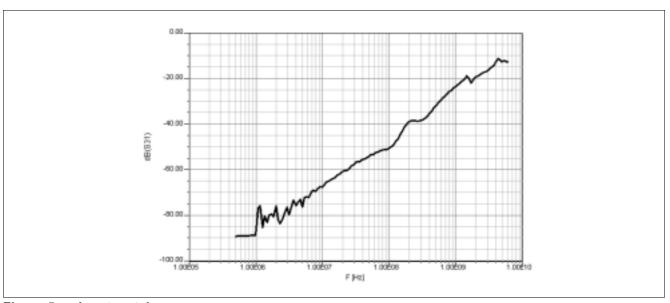


Figure 5 Input match

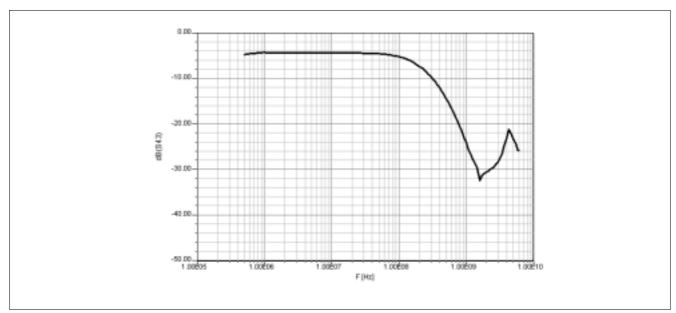


Figure 6 Output-match

Table 2 Measured noise figure

						ī															
f/GHz	1.0	1.1	12	13	1 4	15	16	17	1 8	19	20	21	22	23	24	25	26	2.7	28	29	3.0
J/ OI 12	1.0		1.2	1.0	1	1.0	1.0	1.7	1.0	1.0	2.0	۲. ۱	2.2	2.0	2.7	2.0	2.0	2.,	2.0	2.0	0.0
MEIAD	1.4	1.4	16	1 5	1 1	1 1	1 1	1 1	1 1	1 1	1 1	1 5	1 5	1 5	1 1	1 1	1 1	1.4	1 1	1 5	16
IVITIUD	1.4	1.4	1.0	1.5	1.4	1.4	1.4	1.4	1.4	1.4	1.4	1.0	1.5	1.5	1.4	1.4	1.4	1.4	1.4	1.5	1.0

Application Note 7 Rev. 2.0, 2007-01-08